

VRFA0043V2 - BD

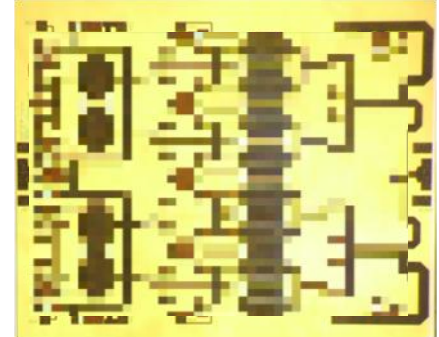


X-band 9W GaAs MMIC Power Amplifier

Preliminary Datasheet v1

Features

- Frequency Range: 8.5 to 11GHz
- Saturated CW Output Power 9W typical
- Saturated Efficiency 50% typical
- Bias: $V_d = 8V$, $I_{dq} = 2.7A$ typical
- Engineering Die Size: 4 x 4.5 x 0.1 mm
- Production Die Size: 4 x 3 x 0.1 mm



Description

The VRFA0043V2-BD is a 9W CW GaAs high power amplifier MMIC which operates over the frequency range of 8.5GHz to 11GHz. The amplifier typically delivers a small signal gain of +21dB, saturated output power P_{sat} of +39.5dBm with a typical efficiency of 45%. The RF ports are DC blocked and matched to 50Ω. Typical applications for the VRFA0043V2-BD include radar and test and instrumentation.

Electrical Specifications

$T = +25^{\circ}C$ baseplate, $V_{DD} = +8V$, $I_{dq} = 2.7A$

Parameter	Specification			Unit
	Max.	Typ.	Min.	
Frequency Bandwidth	8.5		11	GHz
Small Signal Gain		21		dB
CW Saturated Output Power (P_{sat})		39.5		dBm
I/P Return Loss		-8		dB
O/P Return Loss		-10		dB
CW Power Added Efficiency (PAE)		45		%

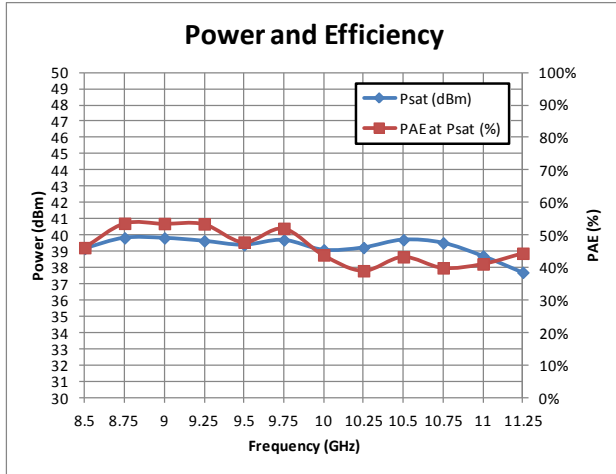
VRFA0043V2 - BD



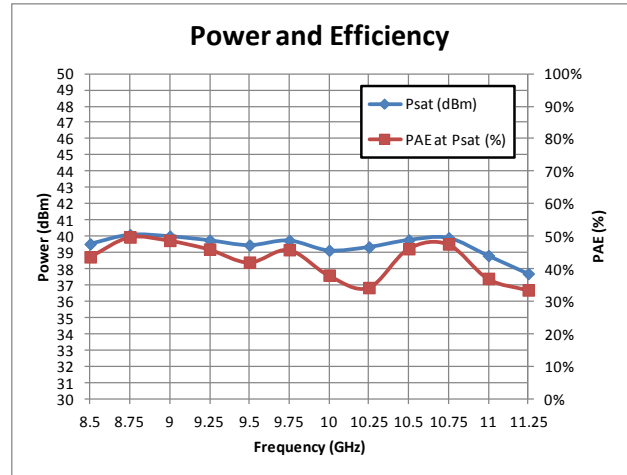
X-band 9W GaAs MMIC Power Amplifier

Preliminary Datasheet v1

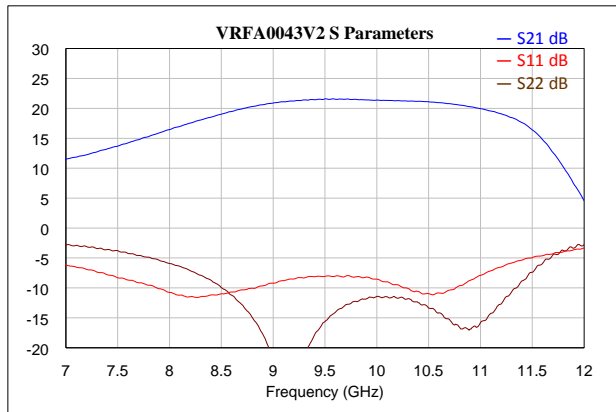
Measured Performance (T=+25°C baseplate, CW signal) in Test Fixture



$V_{D1} = +5V, I_{DQ1} = 0.6A, V_{D2} = +8V, I_{DQ2} = 2.05A$



$V_{D1} = +8V, I_{DQ1} = 0.63A, V_{D2} = +8V, I_{DQ2} = 2.1A$



$V_{D1} = +8V, I_{DQ1} = 0.42A, V_{D2} = +8V, I_{DQ2} = 1.35A$

VRFA0043V2 - BD



X-band 9W GaAs MMIC Power Amplifier

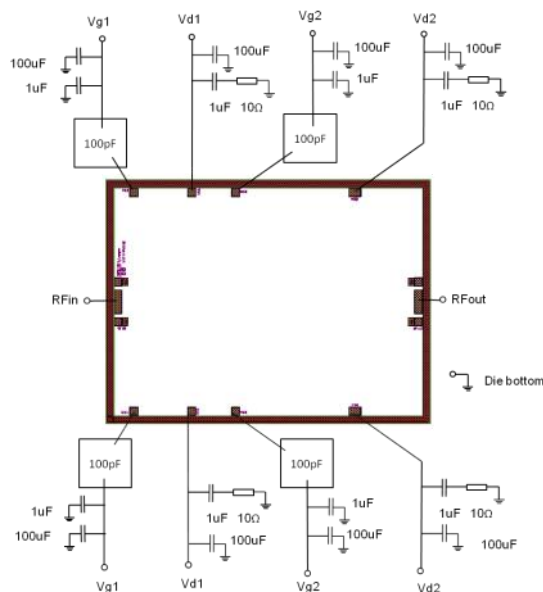
Preliminary Datasheet v1

Recommended Absolute Maximum Ratings ^[1]

Parameter	Symbol	Value	Notes
Drain Bias Voltage	V_d	+10V	
Gate Bias Voltage	V_g	-5V	
Gate Current	I_g	20mA	
RF input power	RF_{in}	20dBm	
Power Dissipation	P_d		Related to Junction Temperature
Junction Temperature	T_j	200°C	For maximum median device lifetime, T_j should be minimised
Storage temperature	$T_{storage}$	-55 to 150°C	

^[1] Operation outside these conditions may cause permanent damage to the device. Combination of maximum rating conditions may reduce the values. Device performance at these ratings is not implied.

Assembly & Bonding Diagram



Engineering Die Size	4mm x 4.5mm
Die Thickness	100µm
Minimum Bondpad opening	70µm x 70µm

Minimal length (0.15nH) are recommended for RF bondwires. The RF input and output ports are DC blocked.

GaAs devices are ESD sensitive and precautions should be observed during storage, handling, assembly and testing.

